

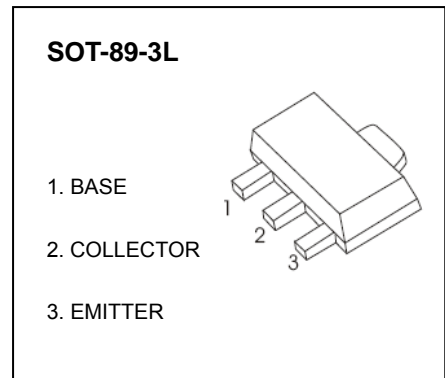


# SOT-89-3L Plastic-Encapsulate Transistors

**KTC4373** TRANSISTOR (NPN)

**FEATURES**

- Small Flat Package
- High Voltage Application
- High Voltage
- High Transition Frequency



**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	120	V
V <sub>CEO</sub>	Collector-Emitter Voltage	120	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current	800	mA
P <sub>C</sub>	Collector Power Dissipation	500	mW
R <sub>θJA</sub>	Thermal Resistance From Junction To Ambient	250	°C/W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 1mA, I <sub>E</sub> =0	120			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =0	120			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =1mA, I <sub>C</sub> =0	5			V
Collector cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> =120V, I <sub>E</sub> =0			100	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0			100	nA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =100mA	80		240	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA			1	V
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =500mA			1	V
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz			30	pF
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> = 500mA		120		MHz

**CLASSIFICATION OF h<sub>FE</sub>**

RANK	O	Y
RANGE	80 - 160	120 - 240
MARKING	CO	CY